



# The LHCb Vertex Locator

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- LHCb and its Vertex Locator
- Radiation Environment
- Technology Choices
- Current Status
- Upgrade Possibilities





One of four experiments at LHC:

- @ CERN, Geneva
- Commissioned April 2007
- 14 TeV p-p collisions at 40 MHz
  - $\rightarrow$  25 ns read-out time
- Study the physics of **b**-flavoured hadrons (CP-violation)



Kinematical constraints  $\rightarrow$  majority of b-hadrons produced in the direction close to the beam-line



Primary and secondary vertex resolution

- $\rightarrow$  Characteristic of b-hadrons
  - Flight path in the order of mm
  - $\bullet$  Measured with precision of 100  $\mu m$

Single spectrometer arm

 $\rightarrow$  15-300 mrad acceptance









4



×10<sup>11</sup> 1200

Non-uniform radiation environment:

- Peak value: 1.3 \*  $10^{14} n_{eq} \text{ cm}^{-2} \text{ NIEL per year}$
- Decreases with increasing radius

Particle flux for one year of operation tracking station 7 (1 MeV neutron/cm<sup>2</sup> NIEL equivalent)







- 2 silicon types of sensors: R and  $\Phi$  micro-strips 2 x 16 Read-out chips ("Beetle"):  $\rightarrow$  IBM rad-hard deep sub-micron process TPG substrate with carbon fibre frame  $\rightarrow$  Kapton flex circuit laminated on each side Contact for CO<sub>2</sub> cooling Low-mass, high rigidity carbon fibre paddle Precision aluminium base plate
  - Silicon micro-strip sensor:
  - R and  $\Phi$  strips: for computational efficiency and occupancy
  - Pitch: 40-102  $\mu m$  for R and 36-97  $\mu m$  for  $\Phi$
  - Read-out chips out of acceptance
  - Double metal for routing lines
  - Silicon operating temperature: -5 °C





# Technology choices (1)



Diffusion Oxygenated Float Zone Silicon (DOFZ) is shown to be more resistant to charged particle radiation.

VELO will use thin (200-300  $\mu m)$  DOFZ sensors produced by MICRON

Depletion voltage vs. particle fluence, 1 MeV NIEL equivalent. From ROSE collaboration (NIM A 466 pp 308-326)





Beetle 1.3 front-end chip

- IBM 0.25 µm CMOS process
- Rad-hard design rules
- Qualified > 30 MRad

IWORID (July 28, 2004)



## Technology choices (2)





IWORID (July 28, 2004)



### Current Status





Final stage of R/D

- Evaluation of a final prototype in beam-test (June 04)
- Irradiation and sub-sequent measurements in the fall







Cz detector in the beam-line

# VELO upgrade scenarios (1)



VELO Silicon foreseen to last ~ 3 years

- $\rightarrow$  LHC will operate ~ 10 years
- $\rightarrow$  Performance upgrade

Many different upgrade scenarios under discussion  $\rightarrow$  n-on-p, 3D, Cz silicon, strixels, pixels ...

#### One option: Magnetic Czochralski (Cz) silicon

- Alternative to float-zone silicon widely available in industry
- Naturally high oxygen levels: ~10<sup>18</sup> cm<sup>-3</sup> (Cf. DOFZ ~10<sup>17</sup> cm<sup>-3</sup>)
- Expected to be radiation hard

#### First beam-test of a large micro-strip Cz sensor with 40 MHz read-out

- 380 µm sensor, parallel 50 µm strips
- p-on-n
- · Measured before and after irradiation



## VELO upgrade scenarios (2)



Most Probable Signal as a function of Bias Voltage, Unirradiated Cz **50** counts] **Results:** 45 40 • S/N before irradiation: 23.5 ± 2.5 for 380 μm • S/N after irradiation: 11 for 380 µm **Most Probable** 25  $\rightarrow$  Corresponding to two years of VELO operation 20  $\rightarrow$  Under-depleted 15  $\rightarrow$  Low statistics 10 5 0 300 400 500 600 700 80 Czochralski Bias Voltage [V] 800 100 200 Most Probable Signal as a function of Bias Voltage st 220 200 200 7x10^14 p/cm^2 200 4.25x10^14 p/cm^2 0<sup>200</sup> Q 180 1.25x10^14 p/cm^2 lang 140 140 We aim to continue investigating this **Most Probable** 120 track as a possibility for a VELO upgrade -100 80 -0-60 40 20 0Ê 50 100 150 200 250 300 350 400 450 500

Czochralski Bias Voltage [V]





LHCb Vertex Locator

- Exciting application of rad-hard silicon sensors
- Technology choices (DOFZ and n-on-n)
- Final R/D phase commissioned April 2007
- Vision of one upgrade track